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ID	Output Current(D.C.)	Tc=85	110	A
IFSM	Surge forward current	t=10mS Tvj =45	2250	A
i ² t	Circuit Fusing Consideration		25000	A ² s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
Tvj	Operating Junction Temperature		-40 to +125	
Tstg	Storage Temperature		-40 to +125	
Mt	Mounting Torque	To terminals(M5)	3±15%	Nm
Ms		To heatsink(M6)	5±15%	Nm
Weight	Module ˆApproximately ˆ		100	g

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Symbol	Parameter	Conditions	Value	Unit
I_{TAV}	Average On-State Current	Sine 180°; $T_c=85$	110	A
I_{TSM}	Surge On-State Current	$T_{VJ}=45$ $t=10ms$, sine $T_{VJ}=125$ $t=10ms$, sine	2250 1900	A
i^2t	Circuit Fusing Consideration	$T_{VJ}=45$ $t=10ms$, sine $T_{VJ}=125$ $t=10ms$, sine	25000 18000	A ² s
V_{isol}	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T_{vj}	Operating Junction Temperature		-40 to +130	
T_{stg}	Storage Temperature		-40 to +125	
M_t	Mounting Torque	To terminals(M5)	3 f 15%	Nm
M_s		To heatsink(M6)	5 f 15%	Nm
di/dt	Critical Rate of Rise of On-State Current	$T_{VJ}=T_{VJM}$, $2/3V_{DRM}$, $I_G=500mA$ $Tr<0.5\mu s$, $tp>6\mu s$	150	A/ μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_J=T_{VJM}$, $2/3V_{DRM}$ linear voltage rise	1000	V/ μs
a	Maximum allowable acceleration		50	m/s ²

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Symbol	Parameter	Conditions	Value	Unit
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case	0.28	/W
$R_{th(c-s)}$	Thermal Impedance, max.	Case to Heatsink	0.20	/W

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Symbol	Parameter	Conditions	Value	Unit
			M	



